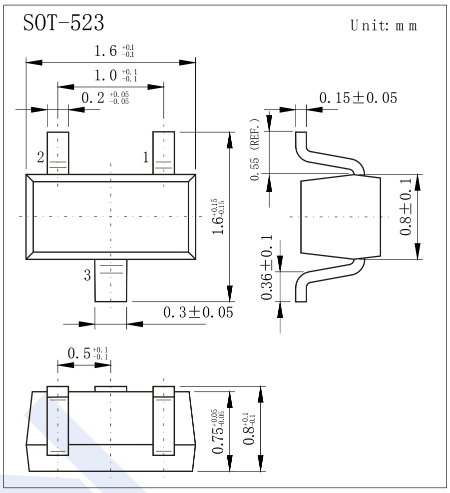
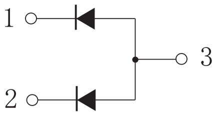
Switching Diodes

DAP222 (KAP222)



■ Features

- ● High speed
- ● Suitable for high packing density layout
- ● High reliability



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	V_{RM}	80	V
DC Reverse Voltage	V_R	80	
Average forward current	I_O	100	mA
Peak Forward Surge Current	I_{FM}	300	
Power Dissipation	P_d	150	mW
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	I_R= 100 uA	80			V
Forward voltage	V_F	I_F= 100mA			1.2	
Reverse voltage leakage current	I_R	V_R= 70 V			0.1	uA
Junction capacitance	C_j	V_R= 6 V, f= 1 MHz			3.5	pF
Reverse recovery time	t_{rr}	I_F=I_R=5mA , V_R=6V			4	ns

■ Marking

Marking	P